

N-channel TrenchMOS SiliconMAX standard level FET Rev. 04 — 20 December 2010 Product de

Product data sheet

Product profile 1.

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC converters

Switched-mode power supplies

1.4 Quick reference data

Table 1.	Quick reference da	ita				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	200	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-	-	20	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	-	150	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	120	130	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A};$ $V_{DS} = 160 \text{ V}; T_j = 25 \text{ °C}$	-	22	-	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	_	_
2	D	drain ^[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN130-200D	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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Limiting values 4.

Limiting values Table 4.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Мах	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	200	V
drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	200	V
gate-source voltage		-20	20	V
drain current	V _{GS} = 10 V; T _{mb} = 100 °C	-	14	А
	V _{GS} = 10 V; T _{mb} = 25 °C	-	20	А
peak drain current	pulsed; T _{mb} = 25 °C	-	80	А
total power dissipation	T _{mb} = 25 °C	-	150	W
storage temperature		-55	175	°C
junction temperature		-55	175	°C
diode				
source current	T _{mb} = 25 °C	-	20	А
peak source current	pulsed; T _{mb} = 25 °C	-	80	А
ggedness				
non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_D = 19 \text{ A}; \\ V_{sup} \leq 25 \text{ V}; \text{ unclamped}; t_p = 100 \mu\text{s}; \\ R_{GS} = 50 \Omega $	-	252	mJ
non-repetitive avalanche current	$V_{sup} \le 25$ V; $V_{GS} = 10$ V; $T_{j(init)} = 25$ °C; R _{GS} = 50 Ω; unclamped	-	20	А
	drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature diode source current peak source current ggedness non-repetitive drain-source avalanche energy	$\begin{array}{ll} drain-source \ voltage & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} \\ drain-gate \ voltage & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega \\ \\ gate-source \ voltage & \\ drain \ current & \frac{V_{GS} = 10 \ \text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C} \\ \hline V_{GS} = 10 \ \text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ peak \ drain \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ storage \ temperature & \\ junction \ temperature & \\ \\ \hline diode & \\ \\ source \ current & T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ \\ \hline ggedness & \\ \\ non-repetitive \ drain-source & \\ \\ v_{Sup} \leq 25 \ \text{V}; \ unclamped; \ t_{p} = 100 \ \mu\text{s}; \\ \\ R_{GS} = 50 \ \Omega \\ \\ \\ non-repetitive \ avalanche & \\ \hline V_{sup} \leq 25 \ \text{V}; \ V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \\ \end{array}$	$\begin{array}{cccc} drain-source voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C} & - & \\ drain-gate voltage & T_j \geq 25 \ ^{\circ}\text{C}; \ T_j \leq 175 \ ^{\circ}\text{C}; \ R_{GS} = 20 \ \text{k}\Omega & - & \\ gate-source voltage & & -20 \\ drain current & V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 100 \ ^{\circ}\text{C} & - & \\ \hline V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ \hline V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ \hline peak \ drain \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ storage \ temperature & & -55 \\ junction \ temperature & & -55 \\ \hline diode & & \\ source \ current & T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}\text{C} & - & \\ \hline ggedness & & \\ non-repetitive \ drain-source & V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ I_D = 19 \ ^{\circ}\text{A}; & - & \\ v_{sup} \ \leq 25 \ ^{\circ}\text{U}; \ unclamped; \ t_p = 100 \ ^{\circ}\text{J}; \\ non-repetitive \ avalanche \ V_{sup} \ \leq 25 \ ^{\circ}\text{V}; \ V_{GS} = 10 \ ^{\circ}\text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ - & \\ \end{array}$	$\begin{array}{cccc} drain-source \ voltage & T_j \geq 25 \ ^{\circ}C; \ T_j \leq 175 \ ^{\circ}C & - & 200 \\ drain-gate \ voltage & T_j \geq 25 \ ^{\circ}C; \ T_j \leq 175 \ ^{\circ}C; \ R_{GS} = 20 \ k\Omega & - & 200 \\ gate-source \ voltage & & -20 & 20 \\ drain \ current & V_{GS} = 10 \ ^{\circ}T_{mb} = 100 \ ^{\circ}C & - & 14 \\ \hline V_{GS} = 10 \ ^{\circ}T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ drain \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}C & - & 80 \\ total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}C & - & 150 \\ storage \ temperature & & -55 & 175 \\ junction \ temperature & & -55 & 175 \\ \hline diode & & & & & \\ source \ current & T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & V_{GS} = 10 \ ^{\circ}T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}C & - & 20 \\ peak \ source \ current & pulsed; \ T_{mb} = 25 \ ^{\circ}C & - & 80 \\ \hline ggedness & & & \\ non-repetitive \ drain-source & V_{GS} = 10 \ ^{\circ}T_{j(init)} = 25 \ ^{\circ}C; \ ^{\circ}L_{D} = 19 \ ^{\circ}R_{GS} = 50 \ \Omega \\ non-repetitive \ avalanche \ energy & V_{Sup} \le 25 \ ^{\circ}V_{SGS} = 10 \ ^{\circ}T_{j(init)} = 25 \ ^{\circ}C; \ - & 20 \\ \hline \end{array}$

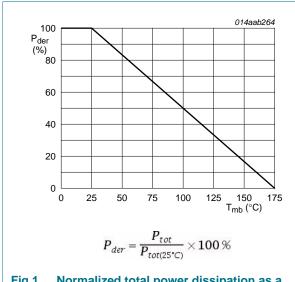
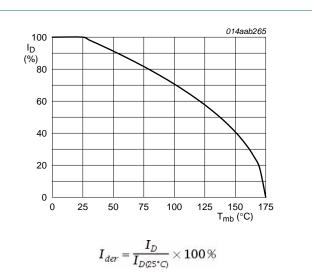


Fig 1. Normalized total power dissipation as a function of mounting base temperature

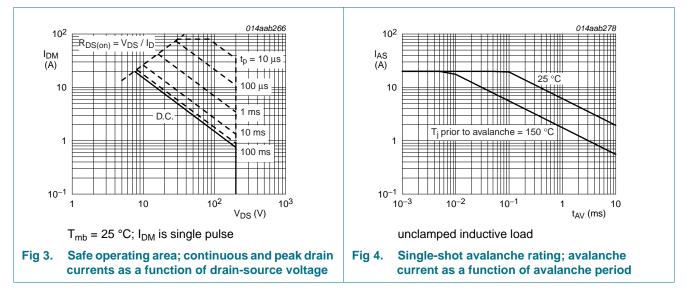




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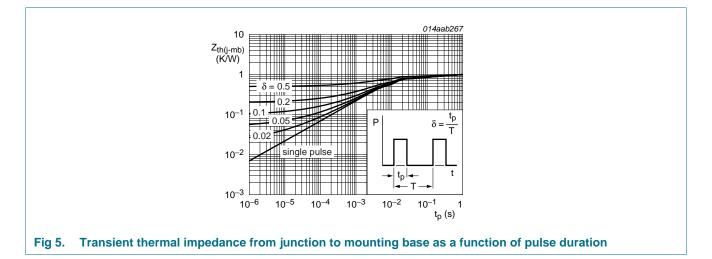
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W



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6. Characteristics

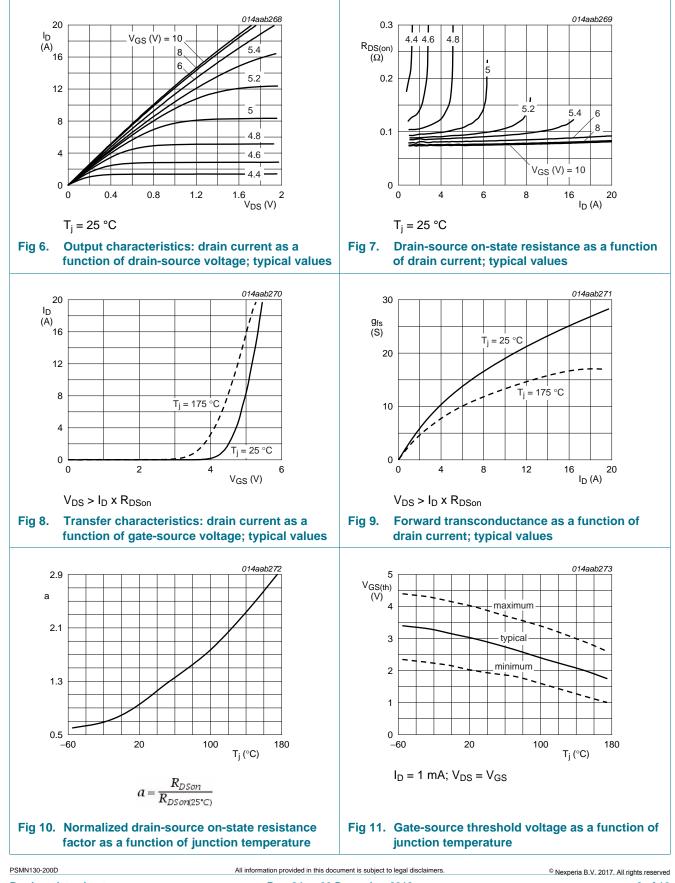
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	178	-	-	V	
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	200	-	-	V
V _{GS(th)}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 150 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 150 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	0.02	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	0.02	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C	-	-	377	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	120	130	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge			65	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	10	-	nC
Q _{GD}	gate-drain charge		-	22	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	2470	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	207	-	pF
C _{rss}	reverse transfer capacitance		-	90	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 100 V; R_{L} = 4.7 Ω ; V_{GS} = 10 V;	-	15	-	ns
t _r	rise time	R _{G(ext)} = 5.6 Ω; T _j = 25 °C	-	46	-	ns
t _{d(off)}	turn-off delay time		-	50	-	ns
t _f	fall time		-	38	-	ns
L _D	internal drain inductance	from tab to centre of die; $T_j = 25 \ ^{\circ}C$	-	3.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.95	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs;	-	124	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 25 V; T _j = 25 °C	-	0.74	-	μC

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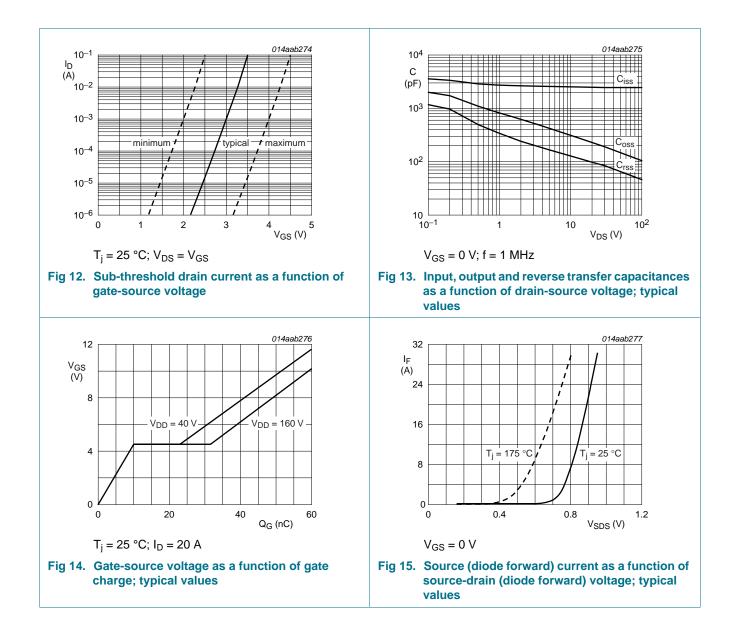
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7. Package outline

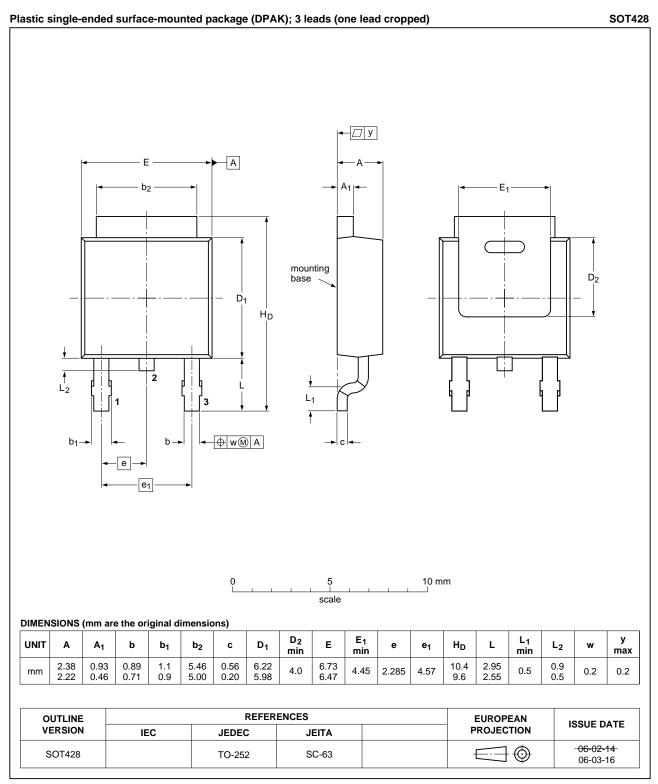


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision hist	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN130-200D v.4	20101220	Product data sheet	-	PSMN130-200D_HG v.3
Modifications:	guidelines of NX	s data sheet has been re P Semiconductors. been adapted to the new to content.	•	
PSMN130-200D_HG v.3	19990801	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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